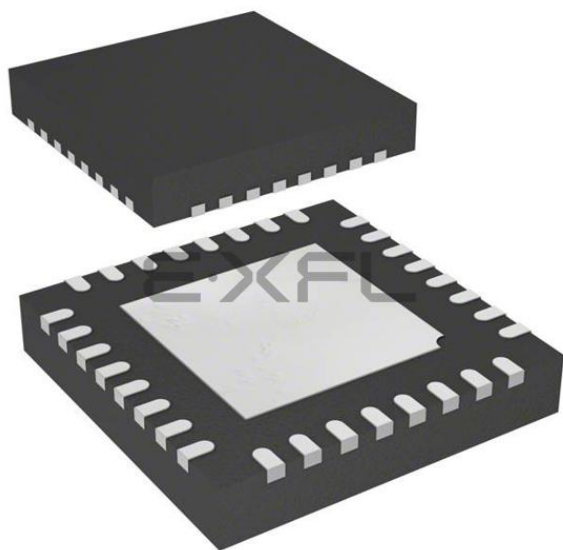




Welcome to [E-XFL.COM](https://www.e-xfl.com)

What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I ² C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	23
Program Memory Size	192KB (192K x 8)
Program Memory Type	FLASH
EEPROM Size	6K x 8
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 10x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-UFQFN Exposed Pad
Supplier Device Package	32-UFQFPN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l082kzu6

Contents

1	Introduction	9
2	Description	10
2.1	Device overview	11
2.2	Ultra-low-power device continuum	13
3	Functional overview	14
3.1	Low-power modes	14
3.2	Interconnect matrix	19
3.3	ARM® Cortex®-M0+ core with MPU	20
3.4	Reset and supply management	21
3.4.1	Power supply schemes	21
3.4.2	Power supply supervisor	21
3.4.3	Voltage regulator	22
3.5	Clock management	22
3.6	Low-power real-time clock and backup registers	25
3.7	General-purpose inputs/outputs (GPIOs)	25
3.8	Memories	26
3.9	Boot modes	26
3.10	Direct memory access (DMA)	27
3.11	Analog-to-digital converter (ADC)	27
3.12	Temperature sensor	27
3.12.1	Internal voltage reference (V_{REFINT})	28
3.13	Digital-to-analog converter (DAC)	28
3.14	Ultra-low-power comparators and reference voltage	29
3.15	Touch sensing controller (TSC)	29
3.16	AES	30
3.17	Timers and watchdogs	31
3.17.1	General-purpose timers (TIM2, TIM3, TIM21 and TIM22)	31
3.17.2	Low-power Timer (LPTIM)	32
3.17.3	Basic timer (TIM6, TIM7)	32
3.17.4	SysTick timer	32

List of tables

Table 1.	Ultra-low-power STM32L082xx device features and peripheral counts	11
Table 2.	Functionalities depending on the operating power supply range	16
Table 3.	CPU frequency range depending on dynamic voltage scaling	16
Table 4.	Functionalities depending on the working mode (from Run/active down to standby)	17
Table 5.	STM32L0xx peripherals interconnect matrix	19
Table 6.	Temperature sensor calibration values	28
Table 7.	Internal voltage reference measured values	28
Table 8.	Capacitive sensing GPIOs available on STM32L082xx devices	30
Table 9.	Timer feature comparison	31
Table 10.	Comparison of I2C analog and digital filters	33
Table 11.	STM32L082xx I ² C implementation	33
Table 12.	USART implementation	34
Table 13.	SPI/I2S implementation	35
Table 14.	Legend/abbreviations used in the pinout table	38
Table 15.	STM32L072xxx pin definition	39
Table 16.	Alternate functions port A	44
Table 17.	Alternate functions port B	45
Table 18.	Alternate functions port C	46
Table 19.	Alternate functions port H	46
Table 20.	Voltage characteristics	50
Table 21.	Current characteristics	51
Table 22.	Thermal characteristics	51
Table 23.	General operating conditions	52
Table 24.	Embedded reset and power control block characteristics	54
Table 25.	Embedded internal reference voltage calibration values	55
Table 26.	Embedded internal reference voltage	55
Table 27.	Current consumption in Run mode, code with data processing running from Flash memory	57
Table 28.	Current consumption in Run mode vs code type, code with data processing running from Flash memory	58
Table 29.	Current consumption in Run mode, code with data processing running from RAM	59
Table 30.	Current consumption in Run mode vs code type, code with data processing running from RAM	60
Table 31.	Current consumption in Sleep mode	61
Table 32.	Current consumption in Low-power run mode	62
Table 33.	Current consumption in Low-power sleep mode	63
Table 34.	Typical and maximum current consumptions in Stop mode	64
Table 35.	Typical and maximum current consumptions in Standby mode	65
Table 36.	Average current consumption during Wakeup	66
Table 37.	Peripheral current consumption in Run or Sleep mode	67
Table 38.	Peripheral current consumption in Stop and Standby mode	69
Table 39.	Low-power mode wakeup timings	69
Table 40.	High-speed external user clock characteristics	71
Table 41.	Low-speed external user clock characteristics	72
Table 42.	HSE oscillator characteristics	73
Table 43.	LSE oscillator characteristics	74
Table 44.	16 MHz HSI16 oscillator characteristics	75

Table 45.	HSI48 oscillator characteristics	76
Table 46.	LSI oscillator characteristics	76
Table 47.	MSI oscillator characteristics	76
Table 48.	PLL characteristics	78
Table 49.	RAM and hardware registers	79
Table 50.	Flash memory and data EEPROM characteristics	79
Table 51.	Flash memory and data EEPROM endurance and retention	79
Table 52.	EMS characteristics	80
Table 53.	EMI characteristics	81
Table 54.	ESD absolute maximum ratings	82
Table 55.	Electrical sensitivities	82
Table 56.	I/O current injection susceptibility	83
Table 57.	I/O static characteristics	84
Table 58.	Output voltage characteristics	86
Table 59.	I/O AC characteristics	87
Table 60.	NRST pin characteristics	88
Table 61.	ADC characteristics	89
Table 62.	R _{AIN} max for f _{ADC} = 16 MHz	91
Table 63.	ADC accuracy	91
Table 64.	DAC characteristics	95
Table 65.	Temperature sensor calibration values	97
Table 66.	Temperature sensor characteristics	97
Table 67.	Comparator 1 characteristics	98
Table 68.	Comparator 2 characteristics	98
Table 69.	TIMx characteristics	99
Table 70.	I2C analog filter characteristics	100
Table 71.	USART/LPUART characteristics	100
Table 72.	SPI characteristics in voltage Range 1	101
Table 73.	SPI characteristics in voltage Range 2	102
Table 74.	SPI characteristics in voltage Range 3	103
Table 75.	USB startup time	105
Table 76.	USB DC electrical characteristics	105
Table 77.	USB: full speed electrical characteristics	106
Table 78.	WLCSP49 - 49-pin, 3.294 x 3.258 mm, 0.4 mm pitch wafer level chip scale package mechanical data	109
Table 79.	WLCSP49 recommended PCB design rules (0.4 mm pitch)	110
Table 80.	LQFP32 - 32-pin, 7 x 7 mm low-profile quad flat package mechanical data	112
Table 81.	UFQFPN32 - 32-pin, 5x5 mm, 0.5 mm pitch ultra thin fine pitch quad flat package mechanical data	114
Table 82.	Thermal characteristics	115
Table 83.	STM32L082xx ordering information scheme	117
Table 84.	Document revision history	118

- **Startup clock**

After reset, the microcontroller restarts by default with an internal 2.1 MHz clock (MSI). The prescaler ratio and clock source can be changed by the application program as soon as the code execution starts.

- **Clock security system (CSS)**

This feature can be enabled by software. If an HSE clock failure occurs, the master clock is automatically switched to HSI and a software interrupt is generated if enabled.

Another clock security system can be enabled, in case of failure of the LSE it provides an interrupt or wakeup event which is generated if enabled.

- **Clock-out capability (MCO: microcontroller clock output)**

It outputs one of the internal clocks for external use by the application.

Several prescalers allow the configuration of the AHB frequency, each APB (APB1 and APB2) domains. The maximum frequency of the AHB and the APB domains is 32 MHz. See [Figure 2](#) for details on the clock tree.

3.17 Timers and watchdogs

The ultra-low-power STM32L082xx devices include three general-purpose timers, one low-power timer (LPTIM), one basic timer, two watchdog timers and the SysTick timer.

[Table 9](#) compares the features of the general-purpose and basic timers.

Table 9. Timer feature comparison

Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary outputs
TIM2, TIM3	16-bit	Up, down, up/down	Any integer between 1 and 65536	Yes	4	No
TIM21, TIM22	16-bit	Up, down, up/down	Any integer between 1 and 65536	No	2	No
TIM6, TIM7	16-bit	Up	Any integer between 1 and 65536	Yes	0	No

3.17.1 General-purpose timers (TIM2, TIM3, TIM21 and TIM22)

There are four synchronizable general-purpose timers embedded in the STM32L082xx device (see [Table 9](#) for differences).

TIM2, TIM3

TIM2 and TIM3 are based on 16-bit auto-reload up/down counter. It includes a 16-bit prescaler. It features four independent channels each for input capture/output compare, PWM or one-pulse mode output.

The TIM2/TIM3 general-purpose timers can work together or with the TIM21 and TIM22 general-purpose timers via the Timer Link feature for synchronization or event chaining. Their counter can be frozen in debug mode. Any of the general-purpose timers can be used to generate PWM outputs.

TIM2/TIM3 have independent DMA request generation.

These timers are capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 3 hall-effect sensors.

TIM21 and TIM22

TIM21 and TIM22 are based on a 16-bit auto-reload up/down counter. They include a 16-bit prescaler. They have two independent channels for input capture/output compare, PWM or one-pulse mode output. They can work together and be synchronized with the TIM2/TIM3, full-featured general-purpose timers.

They can also be used as simple time bases and be clocked by the LSE clock source (32.768 kHz) to provide time bases independent from the main CPU clock.

3.18.2 Universal synchronous/asynchronous receiver transmitter (USART)

The four USART interfaces (USART1, USART2, USART4 and USART5) are able to communicate at speeds of up to 4 Mbit/s.

They provide hardware management of the CTS, RTS and RS485 driver enable (DE) signals, multiprocessor communication mode, master synchronous communication and single-wire half-duplex communication mode. USART1 and USART2 also support SmartCard communication (ISO 7816), IrDA SIR ENDEC, LIN Master/Slave capability, auto baud rate feature and has a clock domain independent from the CPU clock, allowing to wake up the MCU from Stop mode using baudrates up to 42 Kbaud.

All USART interfaces can be served by the DMA controller.

[Table 12](#) for the supported modes and features of USART interfaces.

Table 12. USART implementation

USART modes/features ⁽¹⁾	USART1 and USART2	USART4 and USART5
Hardware flow control for modem	X	X
Continuous communication using DMA	X	X
Multiprocessor communication	X	X
Synchronous mode ⁽²⁾	X	X
Smartcard mode	X	-
Single-wire half-duplex communication	X	X
IrDA SIR ENDEC block	X	-
LIN mode	X	-
Dual clock domain and wakeup from Stop mode	X	-
Receiver timeout interrupt	X	-
Modbus communication	X	-
Auto baud rate detection (4 modes)	X	-
Driver Enable	X	X

1. X = supported.

2. This mode allows using the USART as an SPI master.

3.18.3 Low-power universal asynchronous receiver transmitter (LPUART)

The devices embed one Low-power UART. The LPUART supports asynchronous serial communication with minimum power consumption. It supports half duplex single wire communication and modem operations (CTS/RTS). It allows multiprocessor communication.

The LPUART has a clock domain independent from the CPU clock. It can wake up the system from Stop mode using baudrates up to 46 Kbaud. The Wakeup events from Stop mode are programmable and can be:

- Start bit detection
- Or any received data frame
- Or a specific programmed data frame

Table 15. STM32L072xxx pin definition (continued)

Pin number			Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions
LQFP32	UFQFPN32 ⁽¹⁾	WLCSP49						
6	6	E5	PA0	I/O	TTa	-	TIM2_CH1, TSC_G1_IO1, USART2_CTS, TIM2_ETR, USART4_TX, COMP1_OUT	COMP1_INM, ADC_IN0, RTC_TAMP2/WKUP1
7	7	E4	PA1	I/O	FT	-	EVENTOUT, TIM2_CH2, TSC_G1_IO2, USART2_RTS, TIM21_ETR, USART4_RX	COMP1_INP, ADC_IN1
8	8	F6	PA2	I/O	FT	-	TIM21_CH1, TIM2_CH3, TSC_G1_IO3, USART2_TX, LPUART1_TX, COMP2_OUT	COMP2_INM, ADC_IN2
9	9	G7	PA3	I/O	FT	-	TIM21_CH2, TIM2_CH4, TSC_G1_IO4, USART2_RX, LPUART1_RX	COMP2_INP, ADC_IN3
10	10	F5	PA4	I/O	TC	(2)	SPI1_NSS, TSC_G2_IO1, USART2_CK, TIM22_ETR	COMP1_INM, COMP2_INM, ADC_IN4, DAC_OUT1
11	11	G6	PA5	I/O	TC	-	SPI1_SCK, TIM2_ETR, TSC_G2_IO2, TIM2_CH1	COMP1_INM, COMP2_INM, ADC_IN5, DAC_OUT2
12	12	G5	PA6	I/O	FT	-	SPI1_MISO, TIM3_CH1, TSC_G2_IO3, LPUART1_CTS, TIM22_CH1, EVENTOUT, COMP1_OUT	ADC_IN6
13	13	F4	PA7	I/O	FT	-	SPI1_MOSI, TIM3_CH2, TSC_G2_IO4, TIM22_CH2, EVENTOUT, COMP2_OUT	ADC_IN7
14	14	G4	PB0	I/O	FT	-	EVENTOUT, TIM3_CH3, TSC_G3_IO2	ADC_IN8, VREF_OUT

6.3 Operating conditions

6.3.1 General operating conditions

Table 23. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f _{HCLK}	Internal AHB clock frequency	-	0	32	MHz
f _{PCLK1}	Internal APB1 clock frequency	-	0	32	
f _{PCLK2}	Internal APB2 clock frequency	-	0	32	
V _{DD}	Standard operating voltage	BOR detector disabled	1.65	3.6	V
		BOR detector enabled, at power on	1.8	3.6	
		BOR detector disabled, after power on	1.65	3.6	
V _{DDA}	Analog operating voltage (DAC not used)	Must be the same voltage as V _{DD} ⁽¹⁾	1.65	3.6	V
V _{DDA}	Analog operating voltage (all features)	Must be the same voltage as V _{DD} ⁽¹⁾	1.8	3.6	V
V _{DD_USB} B	Standard operating voltage, USB domain ⁽²⁾	USB peripheral used	3.0	3.6	V
		USB peripheral not used	1.65	3.6	
V _{IN}	Input voltage on FT, FTf and RST pins ⁽³⁾	2.0 V ≤ V _{DD} ≤ 3.6 V	-0.3	5.5	V
		1.65 V ≤ V _{DD} ≤ 2.0 V	-0.3	5.2	
	Input voltage on BOOT0 pin	-	0	5.5	
	Input voltage on TC pin	-	-0.3	V _{DD} +0.3	
P _D	Power dissipation at T _A = 85 °C (range 6) or T _A = 105 °C (range 7) ⁽⁴⁾	WLCSP49 package	-	417	mW
		UFQFPN32 package	-	556	
		LQFP32 package	-	333	
		WLCSP49 package	-	104	
		UFQFPN32 package	-	139	
		LQFP32 package	-	83	
T _A	Temperature range	Maximum power dissipation (range 6)	-40	85	°C
		Maximum power dissipation (range 7)	-40	105	
		Maximum power dissipation (range 3)	-40	125	
T _J	Junction temperature range (range 6)	-40 °C ≤ T _A ≤ 85 °	-40	105	
	Junction temperature range (range 7)	-40 °C ≤ T _A ≤ 105 °C	-40	125	
	Junction temperature range (range 3)	-40 °C ≤ T _A ≤ 125 °C	-40	130	

1. It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and normal operation.

2. V_{DD_USB} must respect the following conditions:
 - When V_{DD} is powered on ($V_{DD} < V_{DD_min}$), V_{DD_USB} should be always lower than V_{DD} .
 - When V_{DD} is powered down ($V_{DD} < V_{DD_min}$), V_{DD_USB} should be always lower than V_{DD} .
 - In operating mode, V_{DD_USB} could be lower or higher V_{DD} .
 - If the USB is not used, V_{DD_USB} must range from V_{DD_min} to V_{DD_max} to be able to use PA11 and PA12 as standard I/Os.
3. To sustain a voltage higher than $V_{DD}+0.3V$, the internal pull-up/pull-down resistors must be disabled.
4. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_J max (see [Table 82: Thermal characteristics on page 115](#)).

Table 27. Current consumption in Run mode, code with data processing running from Flash memory

Symbol	Parameter	Condition		f _{HCLK} (MHz)	Typ	Max ⁽¹⁾	Unit
I _{DD} (Run from Flash memory)	Supply current in Run mode code executed from Flash memory	f _{HSE} = f _{HCLK} up to 16MHz included, f _{HSE} = f _{HCLK} /2 above 16 MHz (PLL ON) ⁽²⁾	Range3, Vcore=1.2 V VOS[1:0]=11	1	190	250	μA
				2	345	380	
				4	650	670	
			Range2, Vcore=1.5 V VOS[1:0]=10	4	0,8	0,86	mA
				8	1,55	1,7	
				16	2,95	3,1	
			Range1, Vcore=1.8 V VOS[1:0]=01	8	1,9	2,1	
				16	3,55	3,8	
				32	6,65	7,2	
		MSI clock source	Range3, Vcore=1.2 V VOS[1:0]=11	0,065	39	130	μA
				0,524	115	210	
				4,2	700	770	
		HSI clock source (16MHz)	Range2, Vcore=1.5 V VOS[1:0]=10	16	2,9	3,2	mA
			Range1, Vcore=1.8 V VOS[1:0]=01	32	7,15	7,4	

1. Guaranteed by characterization results at 125 °C, unless otherwise specified.

2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Figure 13. I_{DD} vs V_{DD} , at $T_A = 25\text{ }^\circ\text{C}$, Low-power run mode, code running from RAM, Range 3, MSI (Range 0) at 64 KHz, 0 WS

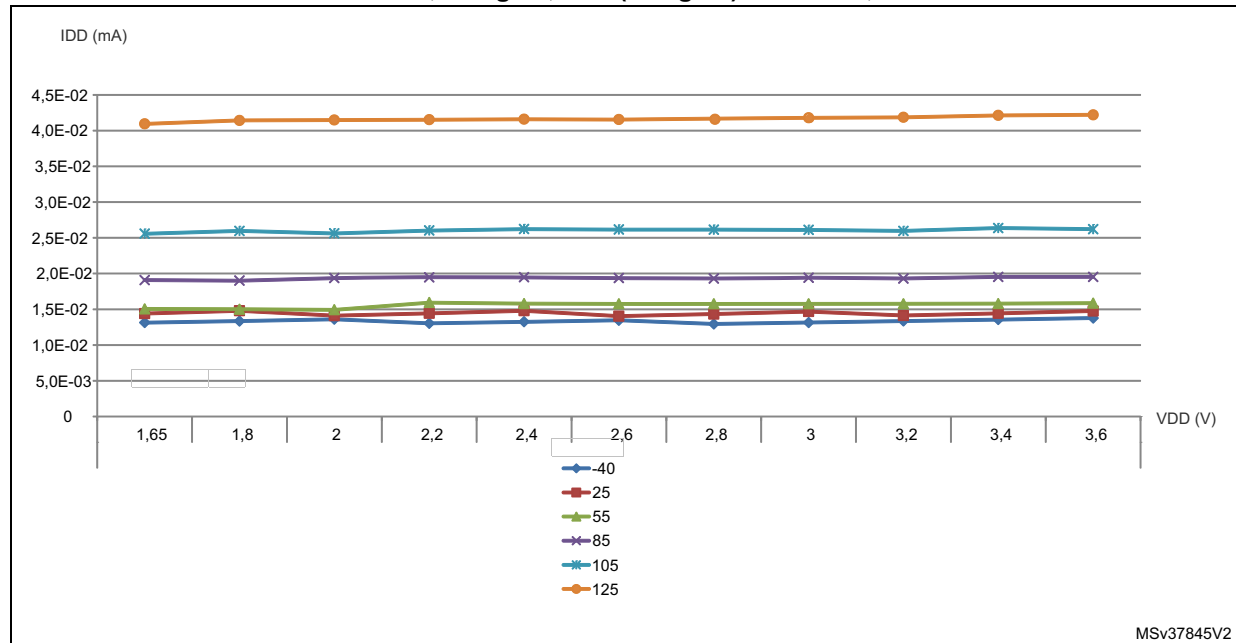


Table 33. Current consumption in Low-power sleep mode

Symbol	Parameter	Condition			Typ	Max (1)	Unit
I_{DD} (LP Sleep)	Supply current in Low-power sleep mode	All peripherals OFF, code executed from Flash memory, V_{DD} from 1.65 to 3.6 V	MSI clock = 65 kHz, $f_{HCLK} = 32$ kHz, Flash memory OFF	$T_A = -40$ to $25\text{ }^\circ\text{C}$	4,7	-	μA
			MSI clock = 65 kHz, $f_{HCLK} = 32$ kHz	$T_A = -40$ to $25\text{ }^\circ\text{C}$	17	24	
				$T_A = 85\text{ }^\circ\text{C}$	19,5	30	
				$T_A = 105\text{ }^\circ\text{C}$	23	47	
				$T_A = 125\text{ }^\circ\text{C}$	32,5	70	
			MSI clock = 65 kHz, $f_{HCLK} = 65$ kHz	$T_A = -40$ to $25\text{ }^\circ\text{C}$	17	24	
				$T_A = 85\text{ }^\circ\text{C}$	20	31	
				$T_A = 105\text{ }^\circ\text{C}$	23,5	47	
				$T_A = 125\text{ }^\circ\text{C}$	32,5	70	
			MSI clock = 131kHz, $f_{HCLK} = 131$ kHz	$T_A = -40$ to $25\text{ }^\circ\text{C}$	19,5	27	
				$T_A = 55\text{ }^\circ\text{C}$	20,5	28	
				$T_A = 85\text{ }^\circ\text{C}$	22,5	33	
				$T_A = 105\text{ }^\circ\text{C}$	26	50	
				$T_A = 125\text{ }^\circ\text{C}$	35	73	

1. Guaranteed by characterization results at $125\text{ }^\circ\text{C}$, unless otherwise specified.

Figure 15. I_{DD} vs V_{DD} , at $T_A = 25/55/85/105/125\text{ }^{\circ}\text{C}$, Stop mode with RTC disabled, all clocks off

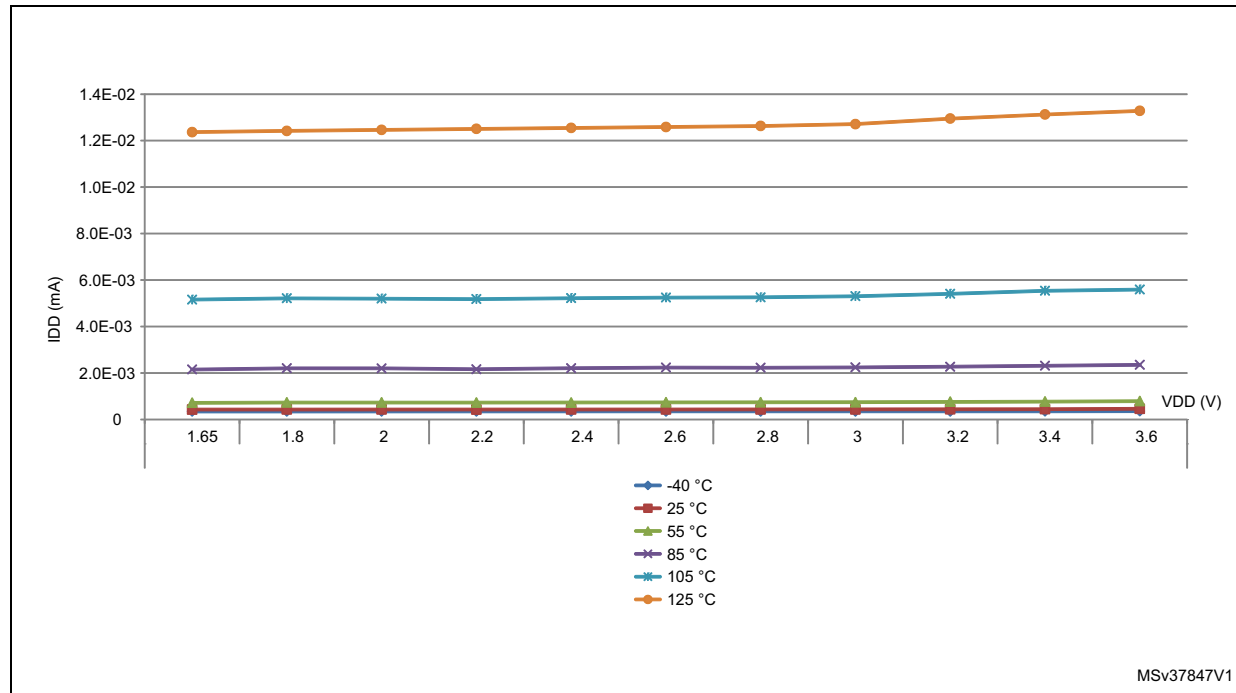


Table 35. Typical and maximum current consumptions in Standby mode

Symbol	Parameter	Conditions		Typ	Max ⁽¹⁾	Unit
I_{DD} (Standby)	Supply current in Standby mode	Independent watchdog and LSI enabled	$T_A = -40\text{ to }25\text{ }^{\circ}\text{C}$	0,855	1,70	μA
			$T_A = 55\text{ }^{\circ}\text{C}$	-	2,90	
			$T_A = 85\text{ }^{\circ}\text{C}$	-	3,30	
			$T_A = 105\text{ }^{\circ}\text{C}$	-	4,10	
			$T_A = 125\text{ }^{\circ}\text{C}$	-	8,50	
		Independent watchdog and LSI off	$T_A = -40\text{ to }25\text{ }^{\circ}\text{C}$	0,29	0,60	
			$T_A = 55\text{ }^{\circ}\text{C}$	0,32	1,20	
			$T_A = 85\text{ }^{\circ}\text{C}$	0,5	2,30	
			$T_A = 105\text{ }^{\circ}\text{C}$	0,94	3,00	
			$T_A = 125\text{ }^{\circ}\text{C}$	2,6	7,00	

1. Guaranteed by characterization results at $125\text{ }^{\circ}\text{C}$, unless otherwise specified

Table 38. Peripheral current consumption in Stop and Standby mode⁽¹⁾

Symbol	Peripheral	Typical consumption, T _A = 25 °C		Unit
		V _{DD} =1.8 V	V _{DD} =3.0 V	
I _{DD} (PVD / BOR)	-	0.7	1.2	μA
I _{REFINT}	-	-	1.7	
-	LSE Low drive ⁽²⁾	0.11	0,13	
-	LSI	0.27	0.31	
-	IWDG	0.2	0.3	
-	LPTIM1, Input 100 Hz	0.01	0,01	
-	LPTIM1, Input 1 MHz	11	12	
-	LPUART1	-	0,5	
-	RTC	0.16	0,3	

1. LPTIM, LPUART peripherals can operate in Stop mode but not in Standby mode.

2. LSE Low drive consumption is the difference between an external clock on OSC32_IN and a quartz between OSC32_IN and OSC32_OUT.-

6.3.5 Wakeup time from low-power mode

The wakeup times given in the following table are measured with the MSI or HSI16 RC oscillator. The clock source used to wake up the device depends on the current operating mode:

- Sleep mode: the clock source is the clock that was set before entering Sleep mode
- Stop mode: the clock source is either the MSI oscillator in the range configured before entering Stop mode, the HSI16 or HSI16/4.
- Standby mode: the clock source is the MSI oscillator running at 2.1 MHz

All timings are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 23](#).

Table 39. Low-power mode wakeup timings

Symbol	Parameter	Conditions	Typ	Max	Unit
t _{WUSLEEP}	Wakeup from Sleep mode	f _{HCLK} = 32 MHz	7	8	Number of clock cycles
t _{WUSLEEP_LP}	Wakeup from Low-power sleep mode, f _{HCLK} = 262 kHz	f _{HCLK} = 262 kHz Flash memory enabled	7	8	
		f _{HCLK} = 262 kHz Flash memory switched OFF	9	10	

High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 1 to 25 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in [Table 42](#). In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 42. HSE oscillator characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{OSC_IN}	Oscillator frequency	-	1		25	MHz
R_F	Feedback resistor	-	-	200	-	k Ω
G_m	Maximum critical crystal transconductance	Startup	-	-	700	$\mu A/V$
$t_{SU(HSE)}^{(2)}$	Startup time	V_{DD} is stabilized	-	2	-	ms

1. Guaranteed by design.
2. Guaranteed by characterization results. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

For C_{L1} and C_{L2} , it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see [Figure 18](#)). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2} . Refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Figure 18. HSE oscillator circuit diagram

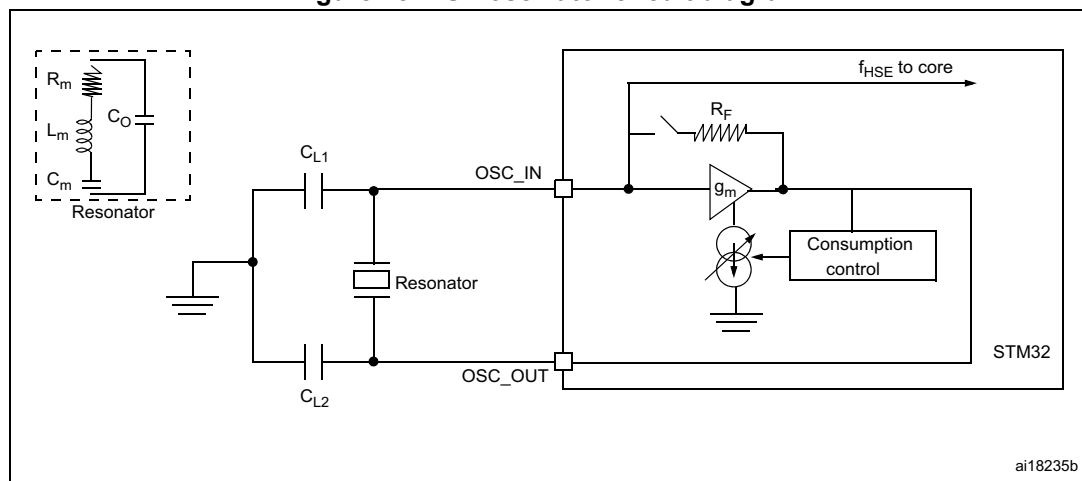
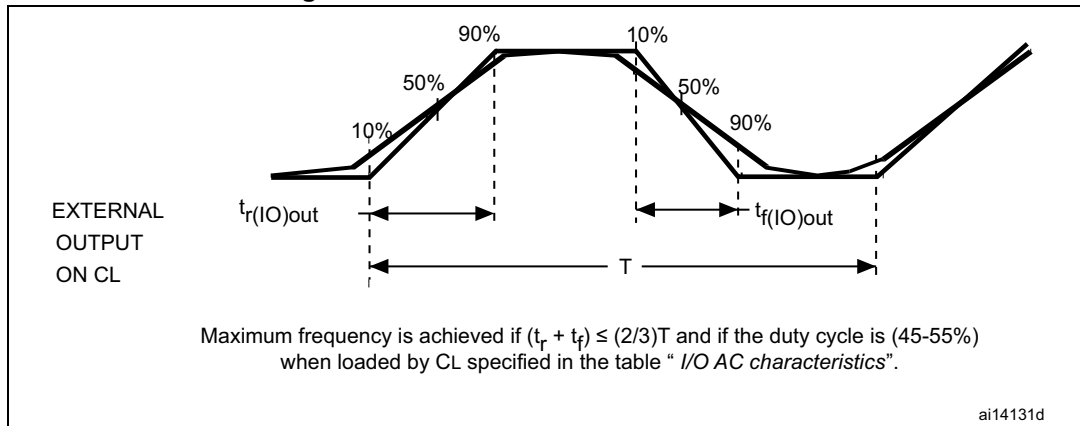


Figure 23. I/O AC characteristics definition



6.3.14 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} , except when it is internally driven low (see [Table 60](#)).

Unless otherwise specified, the parameters given in [Table 60](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 23](#).

Table 60. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{IL(NRST)}^{(1)}$	NRST input low level voltage	-	V_{SS}	-	0.8	V
$V_{IH(NRST)}^{(1)}$	NRST input high level voltage	-	1.4	-	V_{DD}	
$V_{OL(NRST)}^{(1)}$	NRST output low level voltage	$I_{OL} = 2 \text{ mA}$ $2.7 \text{ V} < V_{DD} < 3.6 \text{ V}$	-	-	0.4	
		$I_{OL} = 1.5 \text{ mA}$ $1.65 \text{ V} < V_{DD} < 2.7 \text{ V}$	-	-		
$V_{hys(NRST)}^{(1)}$	NRST Schmitt trigger voltage hysteresis	-	-	$10\%V_{DD}^{(2)}$	-	mV
R_{PU}	Weak pull-up equivalent resistor ⁽³⁾	$V_{IN} = V_{SS}$	30	45	60	k Ω
$V_{F(NRST)}^{(1)}$	NRST input filtered pulse	-	-	-	50	ns
$V_{NF(NRST)}^{(1)}$	NRST input not filtered pulse	-	350	-	-	ns

1. Guaranteed by design.

2. 200 mV minimum value

3. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is around 10%.

Equation 1: R_{AIN} max formula

$$R_{AIN} < \frac{T_S}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The simplified formula above ([Equation 1](#)) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).

Table 62. R_{AIN} max for $f_{ADC} = 16 \text{ MHz}^{(1)}$

T_S (cycles)	t_S (μs)	R_{AIN} max for fast channels ($k\Omega$)	R_{AIN} max for standard channels ($k\Omega$)						
			$V_{DD} > 2.7 \text{ V}$	$V_{DD} > 2.4 \text{ V}$	$V_{DD} > 2.0 \text{ V}$	$V_{DD} > 1.8 \text{ V}$	$V_{DD} > 1.75 \text{ V}$	$V_{DD} > 1.65 \text{ V}$ and $T_A > -10 \text{ }^\circ\text{C}$	$V_{DD} > 1.65 \text{ V}$ and $T_A > 25 \text{ }^\circ\text{C}$
1.5	0.09	0.5	< 0.1	NA	NA	NA	NA	NA	NA
3.5	0.22	1	0.2	< 0.1	NA	NA	NA	NA	NA
7.5	0.47	2.5	1.7	1.5	< 0.1	NA	NA	NA	NA
12.5	0.78	4	3.2	3	1	NA	NA	NA	NA
19.5	1.22	6.5	5.7	5.5	3.5	NA	NA	NA	< 0.1
39.5	2.47	13	12.2	12	10	NA	NA	NA	5
79.5	4.97	27	26.2	26	24	< 0.1	NA	NA	19
160.5	10.03	50	49.2	49	47	32	< 0.1	< 0.1	42

1. Guaranteed by design.

Table 63. ADC accuracy⁽¹⁾⁽²⁾⁽³⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
ET	Total unadjusted error	$1.65 \text{ V} < V_{DDA} = V_{REF+} < 3.6 \text{ V}$, range 1/2/3	-	2	4	LSB
EO	Offset error		-	1	2.5	
EG	Gain error		-	1	2	
EL	Integral linearity error		-	1.5	2.5	
ED	Differential linearity error		-	1	1.5	
ENOB	Effective number of bits		10.2	11	-	bits
	Effective number of bits (16-bit mode oversampling with ratio =256) ⁽⁴⁾		11.3	12.1	-	
SINAD	Signal-to-noise distortion		63	69	-	dB
SNR	Signal-to-noise ratio		63	69	-	
	Signal-to-noise ratio (16-bit mode oversampling with ratio =256) ⁽⁴⁾		70	76	-	
THD	Total harmonic distortion		-	-85	-73	

Table 63. ADC accuracy⁽¹⁾⁽²⁾⁽³⁾ (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
ET	Total unadjusted error	$1.65\text{ V} < V_{\text{REF}+} < V_{\text{DDA}} < 3.6\text{ V}$, range 1/2/3	-	2	5	LSB
EO	Offset error		-	1	2.5	
EG	Gain error		-	1	2	
EL	Integral linearity error		-	1.5	3	
ED	Differential linearity error		-	1	2	
ENOB	Effective number of bits		10.0	11.0	-	bits
SINAD	Signal-to-noise distortion		62	69	-	dB
SNR	Signal-to-noise ratio		61	69	-	
THD	Total harmonic distortion		-	-85	-65	

1. ADC DC accuracy values are measured after internal calibration.
2. ADC Accuracy vs. Negative Injection Current: Injecting negative current on any of the standard (non-robust) analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to standard analog pins which may potentially inject negative current.
Any positive injection current within the limits specified for $I_{\text{INJ(PIN)}}$ and $\Sigma I_{\text{INJ(PIN)}}$ in [Section 6.3.12](#) does not affect the ADC accuracy.
3. Better performance may be achieved in restricted V_{DDA} , frequency and temperature ranges.
4. This number is obtained by the test board without additional noise, resulting in non-optimized value for oversampling mode.

Figure 25. ADC accuracy characteristics

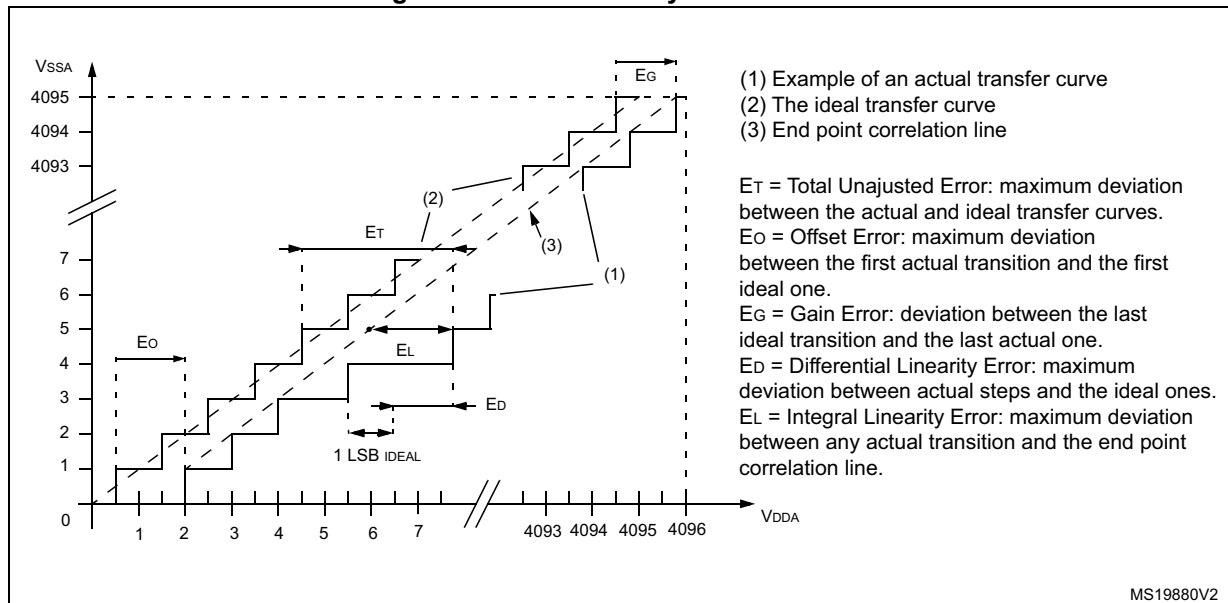


Table 74. SPI characteristics in voltage Range 3 ⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{SCK} $1/t_c(SCK)$	SPI clock frequency	Master mode	-	-	2	MHz
		Slave mode			$2^{(2)}$	
$Duty_{(SCK)}$	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%
$t_{su}(NSS)$	NSS setup time	Slave mode, SPI presc = 2	$4 \cdot T_{pclk}$	-	-	ns
$t_h(NSS)$	NSS hold time	Slave mode, SPI presc = 2	$2 \cdot T_{pclk}$	-	-	
$t_w(SCKH)$ $t_w(SCKL)$	SCK high and low time	Master mode	$T_{pclk} - 2$	T_{pclk}	$T_{pclk} + 2$	
$t_{su}(MI)$	Data input setup time	Master mode	1.5	-	-	
$t_{su}(SI)$		Slave mode	6	-	-	
$t_h(MI)$	Data input hold time	Master mode	13.5	-	-	
$t_h(SI)$		Slave mode	16	-	-	
$t_a(SO)$	Data output access time	Slave mode	30	-	70	
$t_{dis}(SO)$	Data output disable time	Slave mode	40	-	80	
$t_v(SO)$	Data output valid time	Slave mode	-	30	70	
$t_v(MO)$		Master mode	-	7	9	
$t_h(SO)$	Data output hold time	Slave mode	25	-	-	
$t_h(MO)$		Master mode	8	-	-	

1. Guaranteed by characterization results.

2. The maximum SPI clock frequency in slave transmitter mode is determined by the sum of $t_v(SO)$ and $t_{su}(MI)$ which has to fit into SCK low or high phase preceding the SCK sampling edge. This value can be achieved when the SPI communicates with a master having $t_{su}(MI) = 0$ while $Duty_{(SCK)} = 50\%$.

Figure 30. SPI timing diagram - slave mode and CPHA = 0

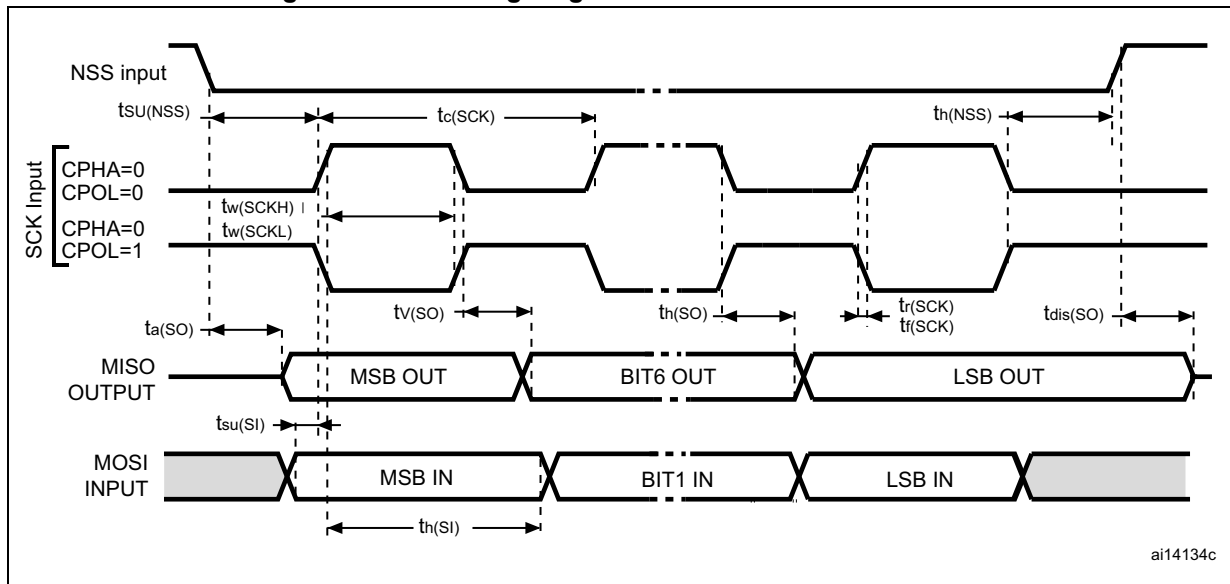
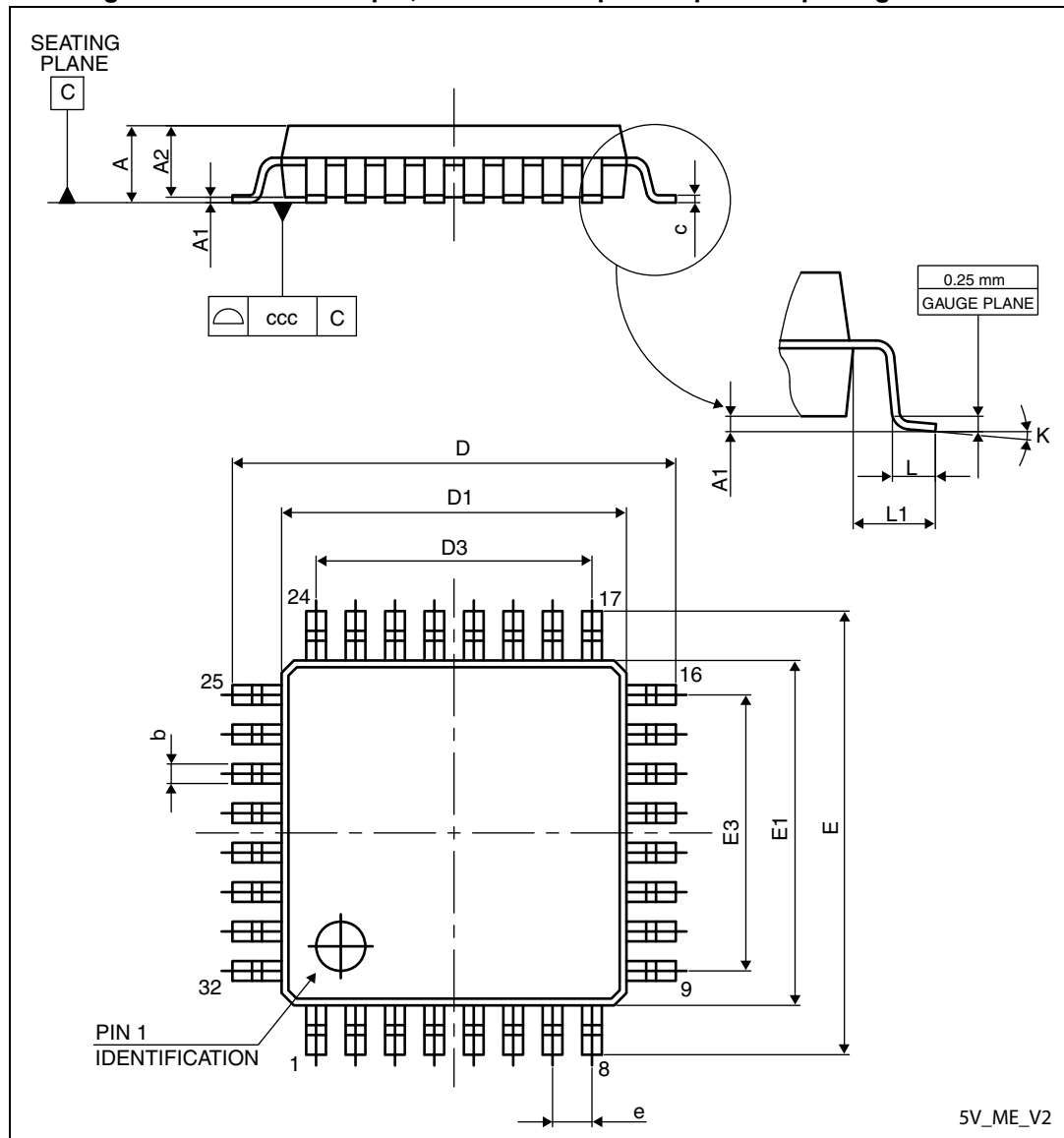


Table 79. WLCSP49 recommended PCB design rules (0.4 mm pitch)

Dimension	Recommended values
Pitch	0.4
Dpad	260 µm max. (circular)
	220 µm recommended
Dsm	300 µm min. (for 260 µm diameter pad)
PCB pad design	Non-solder mask defined via underbump allowed.

7.2 LQFP32 package information

Figure 36. LQFP32 - 32-pin, 7 x 7 mm low-profile quad flat package outline



1. Drawing is not to scale.